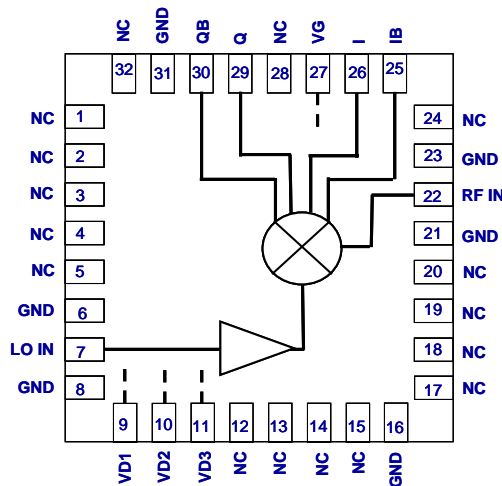


Advance Information: AI1016

**QFN Packaged 10-16GHz Direct Modulator
GaAs Monolithic Microwave IC**

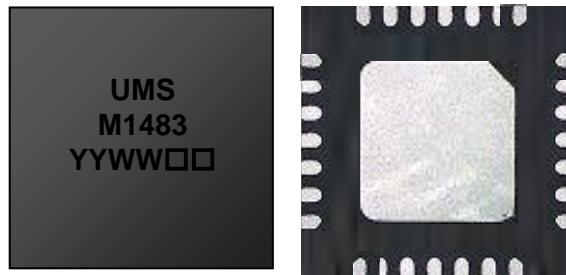


UMS 10-16GHz direct quadrature modulator packaged integrates a double-balanced mixer (LO suppression and Image Rejection) and a LO buffer. It can be used for both LSB and USB configurations. The high carrier suppression, the side band rejection and the very low out-of-band noise density combined with the baseband inputs which supports modulation from DC to 250MHz makes of this circuit a very versatile modulator for high performance systems.

Moreover it is proposed in standard surface mount package (QFN). The overall power supply is as low as 4V / 110mA.

The circuit is mainly dedicated to Point to Point and Point to Multi-Point systems and also well suited for a wide range of microwave and millimetre wave applications and systems.

It is developed on a 0.5µm E/D mode pHEMT process, and will be available in a standard surface mount 32 leads QFN5x5, compliant with the Restriction of Hazardous Substances (RoHS) European Union directive 2002/95/EC.



Main Characteristics

Tamb.= +25°C, VD1 = VD2 = VD3 = +4V

Symbol	Parameter	Min	Typ	Max	Unit
F _{RF}	RF Frequency range	10		16	GHz
F _{LO}	LO Frequency range	10		16	GHz
F _{IF}	Base band bandwidth	DC		250	MHz
G _c	Conversion Gain ⁽¹⁾		-10		dB
P _{LO}	LO input power		0		dBm
LO	Carrier suppression without Vbb tuning		25		dBc
LO sup	Carrier suppression with Vbb tuning		50		dBc
SDB sup	Side band suppression		18		dBc
OIP3	Output IP3		12		dBm
IMD2	2 nd order intermodulation ratio		40		dBc
Spr	Spurious		-55		dBm
Vbb _{I&Ib}	Baseband input DC voltage on I & IB	-0.1		+0.1	V
Vbb _{Q&Qb}	Baseband input DC voltage on Q & QB	-0.1		+0.1	V
VDx	DC supply voltage		4		V
VG	DC mixer supply		-0.7		V
Id	DC supply current		110		mA

⁽¹⁾ Given for V_{IF} = 100mV_{pp} (over 50Ω) on each IF input => Input Power : P_{IF} = -10dBm

These values are representative of on-board measurements.
Electrostatic discharge sensitive device observe handling precautions!

Absolute Maximum Ratings ⁽¹⁾

Tamb.= +25°C

Symbol	Parameter	Values	Unit
Vdx	DC supply voltage	(TBD)	V
Id	DC supply current	(TBD)	mA
VG	DC mixer supply	-2 to +0.4	V
P _{LO}	Maximum P _{LO} peak input power overdrive ⁽²⁾	(TBD)	dBm
P _{IF}	Maximum P _{IF} peak input power overdrive ⁽²⁾	(TBD)	dBm
T _j	Junction temperature	(TBD)	°C
T _a	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-55 to +155	°C

⁽¹⁾ Operation of this device above anyone of these parameters may cause permanent damage.

⁽²⁾ Duration < 1s.

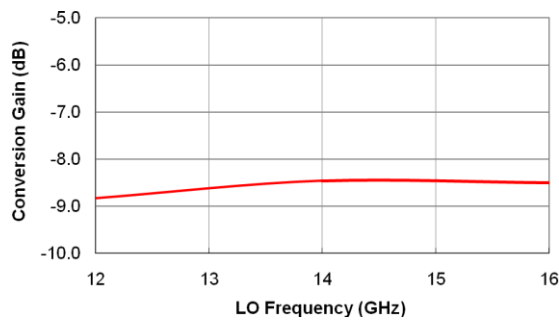
Advanced Information

Typical On Wafer Measurements

Tamb.= +25°C, V_{Dx} = 4V, I_d = 110mA, V_G = -0.7V

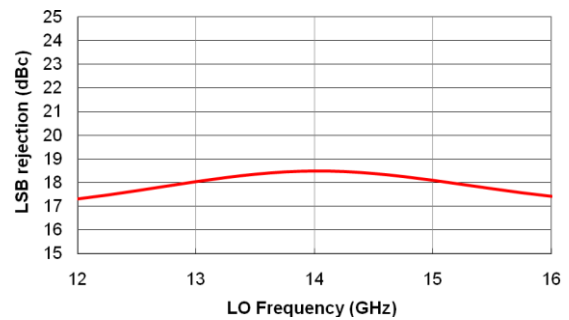
Conversion Gain versus LO frequency

F_{IF} = 9MHz / V_{IF} = 100mVpp
P_{LO} = 0dBm / F_{LO}: 12, 14, 16GHz



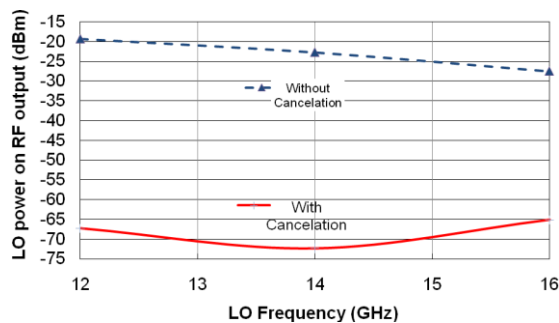
LSB Rejection versus LO frequency

F_{IF} = 9MHz / V_{IF} = 100mVpp
P_{LO} = 0dBm / F_{LO}: 12, 14, 16GHz
V_{bbI&b} and V_{bbQ&Qb} adjusted



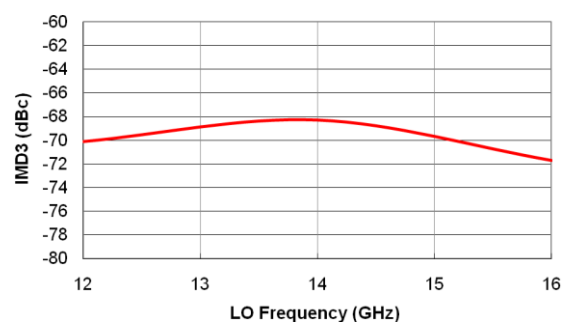
LO Cancelation versus LO frequency

F_{IF} = 9MHz / V_{IF} = 100mVpp
P_{LO} = 0dBm / F_{LO}: 12, 14, 16GHz
V_{bbI&b} and V_{bbQ&Qb} adjusted



IMD3 versus LO frequency

IF₁ = 9 MHz & IF₂ = 11MHz / V_{IF} = 100mVpp
P_{LO} = 0dBm / F_{LO}: 12, 14, 16GHz
P_{RF_DCL} = -18dBm



Advanced Information

Typical On Wafer Measurements

Tamb.= +25°C, VDx = 4V, Id = 110mA, VG = -0.7V

Intermodulation products and Harmonics versus IF frequency

$F_{LO} = 14\text{GHz} / P_{LO} = 0\text{dBm}$

$V_{IF1} = V_{IF2} = 100\text{mVpp}$

$PRF_DCL = -18\text{dBm}$

IF1 & IF2 (MHz)	8 - 10	48 - 50	30 - 50
IMD3 (dBc)	70	65	66
IMD2 _{INF} (dBc)	44	43	48
IMD2 _{SUP} (dBc)	49	41	41
2xRF1 (dBc)	46	35	42
2xRF2 (dBc)	52	35	36

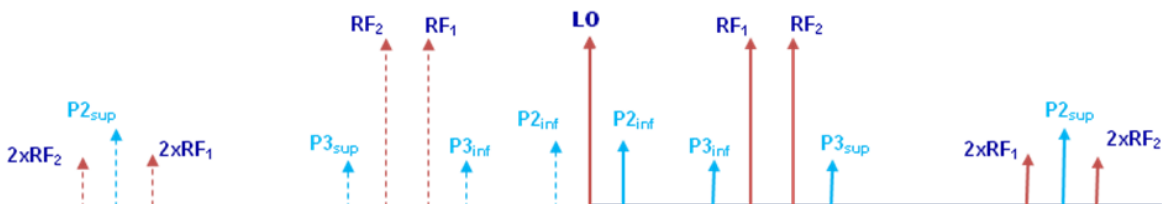
Intermodulation products and Harmonics versus LO frequency

$IF1 = 8\text{MHz} \& IF2 = 10\text{MHz} / V_{IF1} = V_{IF2} = 100\text{mVpp}$

$PRF_DCL = -18\text{dBm}$

FLO (GHz)	13.0	15.0
IMD3 (dBc)	65	66
IMD2 _{INF} (dBc)	39	42
IMD2 _{SUP} (dBc)	39	38
2xRF1 (dBc)	34	34
2xRF2 (dBc)	39	34

Spectral view of Output Intermodulation products and Harmonics

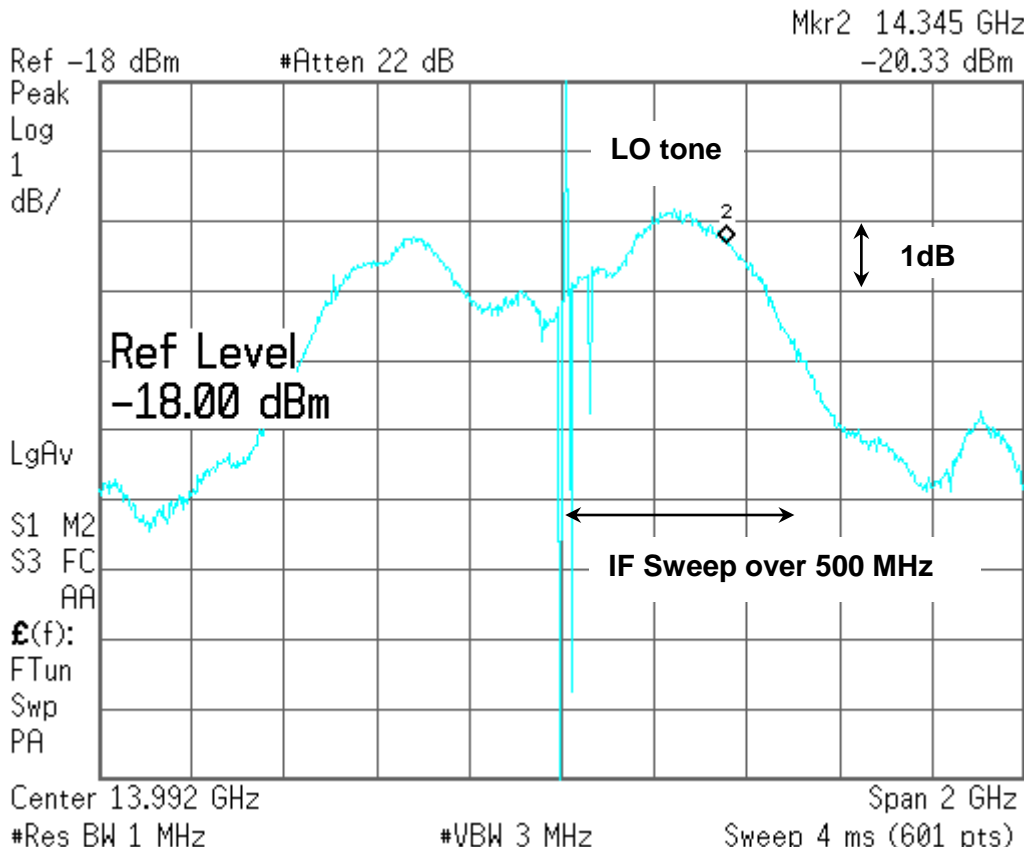


Advanced Information

Typical On Wafer Measurements

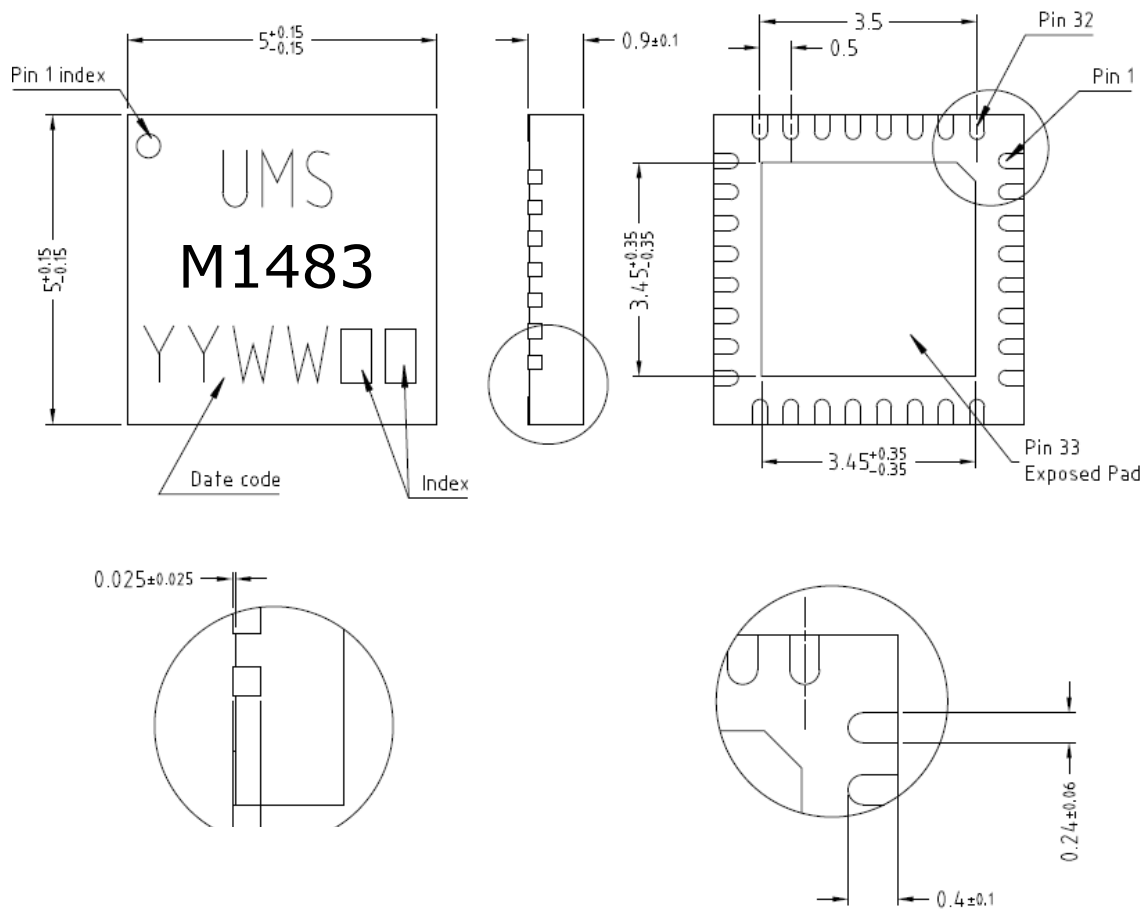
Tamb.= +25°C, V_{Dx} = 4V, I_d = 110mA, V_G = -0.7V

Base band bandwidth (until cut off @1dB)
Spectrum: output RF power on each side of the LO
F_{LO} = 14GHz / V_{IF} = 100mV_{pp}
F_{IF} = DC to 1.0GHz



Advanced Information

Package outline ⁽¹⁾



Matt tin, Lead Free	(Green)	1- Nc	12- Nc	23- Gnd ⁽²⁾
Units :	mm	2- Nc	13- Nc	24- Nc
From the standard :	JEDEC MO-220	3- Nc	14- Nc	25- Ib
	(VHHD)	4- Nc	15- Nc	26- I
	33- GND	5- Nc	16- Gnd ⁽²⁾	27- Vg
		6- Gnd ⁽²⁾	17- Nc	28- Nc
		7- LO in	18- Nc	29- Q
		8- Gnd ⁽²⁾	19- Nc	30- Qb
		9- VD1	20- Nc	31- Gnd ⁽²⁾
		10- VD2	21- Gnd ⁽²⁾	32- Nc
		11- VD3	22- RF in	

⁽¹⁾ The package outline drawing included to this data-sheet is given for indication. Refer to the application note AN0017 (<http://www.ums-gaas.com>) for exact package dimensions.

⁽²⁾ It is strongly recommended to ground all pins marked "Gnd" through the PCB board. Ensure that the PCB board is designed to provide the best possible ground to the package.

Advanced Information

Ref. : AI10161035 - 07 Feb 11

6/8

Subject to change without notice

Notes

Advanced Information

Ref. : AI10161035 - 07 Feb 11

7/8

Subject to change without notice

Recommended package footprint

Refer to the application note AN0017 available at <http://www.ums-gaas.com> for package footprint recommendations and exact package dimensions.

SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017 available at <http://www.ums-gaas.com>.

Recommended environmental management

Refer to the application note AN0019 available at <http://www.ums-gaas.com> for environmental data on UMS package products.

Recommended ESD management

Refer to the application note AN0020 available at <http://www.ums-gaas.com> for ESD sensitivity and handling recommendations for the UMS package products.

Sampling request reference

Package: ES-CHM1483-QFG

Contact us

Web site: www.ums-gaas.com

e.mail: mktsales@ums-gaas.com

Phone: 33 (1) 6933 0226 (France)

1 978 905 3165 (USA)

86 21 6103 1703 (China)

Advanced Information

Ref. : AI10161035 - 07 Feb 11

8/8

Subject to change without notice